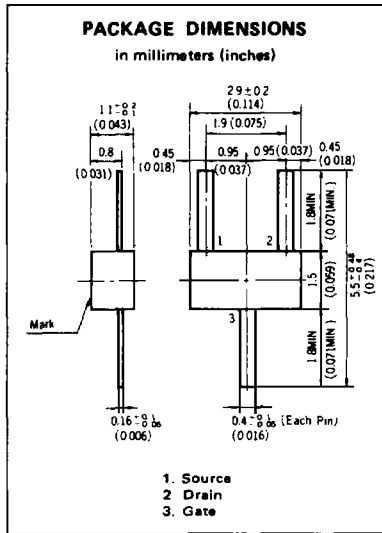


2SK67

Impedance Converter N-channel Silicon Junction FET



- Low zero gate voltage drain current: $I_{DSS} = 200\mu A$ TYP.
- High forward transfer admittance:
 $|Y_{fs2}| = 1500\mu S$ TYP. ($V_{DS} = 5.0V$, $V_{GS} = 0$)

ABSOLUTE MAXIMUM RATINGS

Maximum Voltage and Currents ($T_a = 25^\circ C$)

Gate to Drain Voltage	V_{GDO}	-20	V
Gate Current	I_G	10	mA
Drain Current (DC)	I_D	10	mA

Maximum Power Dissipation

Total Power Dissipation at $25^\circ C$ Ambient Temperature	P_T	80	mW
--	-------	----	----

Maximum Temperatures

Junction Temperature	T_j	100	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to +100	$^\circ C$

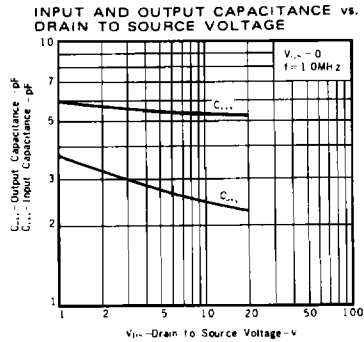
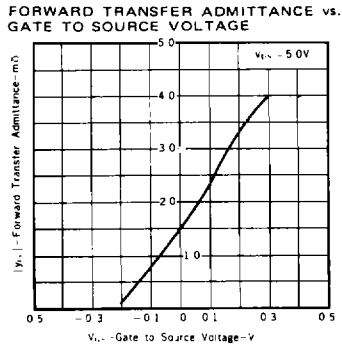
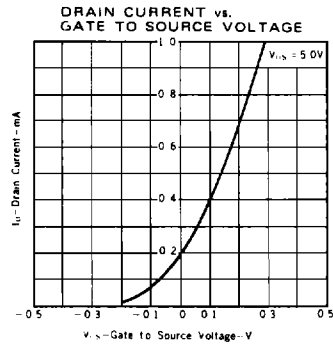
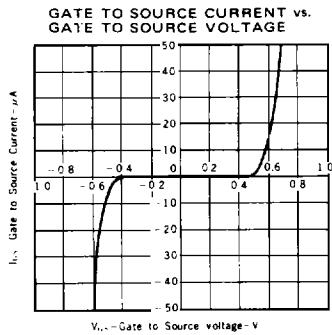
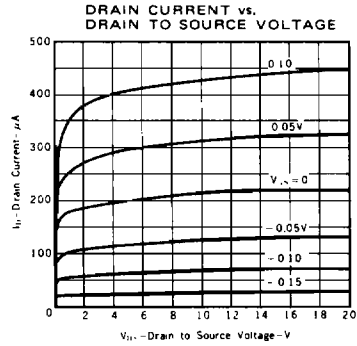
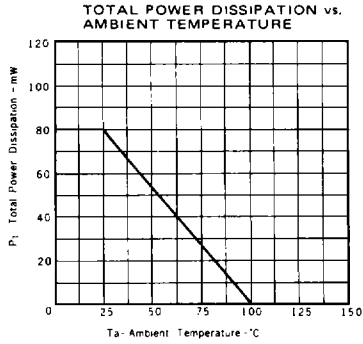
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Zero-Gate-Voltage Drain Current	I_{DSS}	20		1000	μA	$V_{DS} = 5.0V$, $V_{GS} = 0$
Gate-Source Cutoff Voltage	$V_{GS(off)}$			-0.8	V	$V_{DS} = 5.0V$, $I_D = 1.0\mu A$
Forward Transfer Admittance	$ Y_{fs1} $	350			μS	$V_{DS} = 5.0V$, $I_D = 30\mu A$, $f = 1.0kHz$
	$ Y_{fs2} $		1500		μS	$V_{DS} = 5.0V$, $V_{GS} = 0$, $f = 1.0kHz$
Input Capacitance	C_{iss}		5.5		pF	$V_{DS} = 5.0V$, $V_{GS} = 0$, $f = 1.0MHz$
Output Capacitance	C_{oss}		2.7		pF	

I_{DSS} Classification

MARK	J2	J3	J4	J5	J6	J7	J8
$I_{DSS}(\mu A)$	20 - 40	35 - 70	60 - 120	100 - 200	150 - 300	270 - 540	500 - 1000

TYPICAL CHARACTERISTICS (Ta = 25°C)



GATE TO SOURCE CUTOFF VOLTAGE AND FORWARD TRANSFER ADMITTANCE vs. ZERO-GATE-VOLTAGE DRAIN CURRENT

